

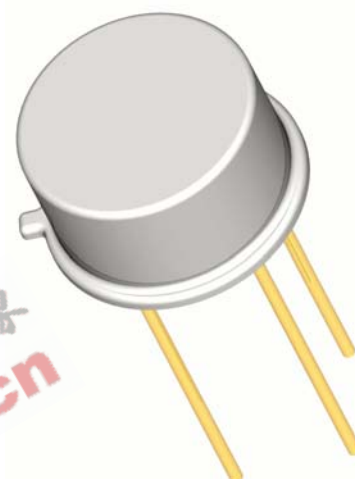
### Description

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N3499LJ)
- JANTX level (2N3499LJX)
- JANTXV level (2N3499LJV)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV
- Radiation testing (total dose) upon request

### Applications

- General purpose
- Low power
- NPN silicon transistor



### Features

- Hermetically sealed TO-5 metal can
- Also available in chip configuration
- Chip geometry 5620
- Reference document: MIL-PRF-19500/366

### Benefits

- Qualification Levels: JAN, JANTX, and JANTXV
- Radiation testing available

Please contact Semicoa for special configurations  
www.SEMICOA.com or (714) 979-1900

Absolute Maximum Ratings		T <sub>c</sub> = 25°C unless otherwise specified	
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	100	Volts
Collector-Base Voltage	V <sub>CBO</sub>	100	Volts
Emitter-Base Voltage	V <sub>EBO</sub>	6	Volts
Collector Current, Continuous	I <sub>C</sub>	500	mA
Power Dissipation, T <sub>A</sub> = 25°C Derate linearly above 25°C	P <sub>T</sub>	1 5.71	W mW/°C
Thermal Resistance	R <sub>θJA</sub>	175	°C/W
Operating Junction Temperature	T <sub>J</sub>	-65 to +200	°C
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C

### ELECTRICAL CHARACTERISTICS

characteristics specified at  $T_A = 25^\circ\text{C}$

Off Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}$	100			Volts
Collector-Base Cutoff Current	$I_{CBO1}$	$V_{CB} = 100\text{ Volts}$			10	$\mu\text{A}$
	$I_{CBO2}$	$V_{CB} = 50\text{ Volts}$			50	nA
	$I_{CBO3}$	$V_{CB} = 50\text{ Volts}, T_A = 150^\circ\text{C}$			50	$\mu\text{A}$
Collector-Emitter Cutoff Current	$I_{CEO}$	$V_{CE} = 80\text{ Volts}$			1	$\mu\text{A}$
Emitter-Base Cutoff Current	$I_{EBO1}$	$V_{EB} = 6\text{ Volts}$			10	$\mu\text{A}$
	$I_{EBO2}$	$V_{EB} = 4\text{ Volts}$			25	nA
On Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	$h_{FE1}$	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ Volts}$	35			
	$h_{FE2}$	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ Volts}$	50			
	$h_{FE3}$	$I_C = 10\text{ mA}, V_{CE} = 10\text{ Volts}$	75			
	$h_{FE4}$	$I_C = 150\text{ mA}, V_{CE} = 10\text{ Volts}$	100			300
	$h_{FE6}$	$I_C = 500\text{ mA}, V_{CE} = 10\text{ Volts}$	20			
	$h_{FE7}$	$I_C = 150\text{ mA}, V_{CE} = 10\text{ Volts}$	45			
			$T_A = -55^\circ\text{C}$			
Base-Emitter Saturation Voltage	$V_{BEsat1}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$			0.8	Volts
	$V_{BEsat3}$	$I_C = 300\text{ mA}, I_B = 30\text{ mA}$			1.4	Volts
Collector-Emitter Saturation Voltage	$V_{CEsat1}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$			0.2	Volts
	$V_{CEsat3}$	$I_C = 300\text{ mA}, I_B = 30\text{ mA}$			0.6	Volts
Dynamic Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{FE} $	$V_{CE} = 20\text{ Volts}, I_C = 20\text{ mA}, f = 100\text{ MHz}$	1.5		8	
Small Signal Short Circuit Forward Current Transfer Ratio	$h_{FE}$	$V_{CE} = 10\text{ Volts}, I_C = 10\text{ mA}, f = 1\text{ kHz}$	75		375	
Open Circuit Output Capacitance	$C_{OBO}$	$V_{CB} = 10\text{ Volts}, I_E = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			10	pF
Open Circuit Input Capacitance	$C_{IBO}$	$V_{EB} = 0.5\text{ Volts}, I_C = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			80	pF
Noise Figure	$NF_1$	$V_{CE} = 10\text{ Volts}, I_C = 0.5\text{ mA}, f = 1\text{ kHz}, R_g = 1\text{ k}\Omega$			16	dB
	$NF_2$	$V_{CE} = 10\text{ Volts}, I_C = 0.5\text{ mA}, f = 10\text{ kHz}, R_g = 1\text{ k}\Omega$			6	dB
Switching Characteristics						
Saturated Turn-On Time	$t_{ON}$	$V_{EB} = 5\text{ Volts}, I_C = 150\text{ mA}, I_{B1} = 15\text{ mA}$			115	ns
Saturated Turn-Off Time	$t_{OFF}$	$I_C = 150\text{ mA}, I_{B1}=I_{B2}=15\text{ mA}$			1,150	ns